

**IN THE SPECIFICATION:**

Please replace paragraph [0009] with the following amended paragraph:

[0009] Figures 1A-1C are schematic diagrams illustrating the phenomena of dishing and nitride loss. Figure 1A shows an example of a patterned STI substrate with a substrate 10, having a thermal oxide layer [[10]] 15 disposed thereon, a polishing/etch stop layer 20, such as silicon nitride, disposed on the thermal oxide layer 15, and patterned to have feature definitions 35. The feature definitions 35 are then filled with a dielectric fill material 30, such as a silicon oxide material, with excess dielectric fill material 40 formed over the feature definitions 35 and silicon nitride layer 20.

Please replace paragraph [0039] with the following amended paragraph:

[0039] The second polishing step may include polishing a substrate with an abrasive-free polishing composition and a fixed-abrasive polishing article. The fixed-abrasive polishing article may be a high removal rate fixed-abrasive web material, for example, the SWR-521 fixed-abrasive polishing article, commercially available from 3M of Minneapolis, Minnesota. The abrasive-free polishing composition may be a high selectivity polishing composition to terminate the polishing process without removal of the second dielectric material. One example of a polishing composition for use with fixed-abrasive polishing articles is a proline or l-proline containing polishing composition which is more fully described in co-pending United States Patent application Serial No. 10/074,345 [~~Atty. Docket No. 6075/CMP/CMP/RLKK~~], filed on February 12, 2002, and entitled "STI Polish Enhancement Using Fixed Abrasives With Amino Acid Additives[["], which is incorporated herein by reference to the extent not inconsistent with the disclosure and claimed aspects herein.

Please replace paragraph [0060] with the following amended paragraph:

[0060] The fixed-abrasive polishing article polishing enhancement process techniques described herein may be used to enhance other known polishing processes using fixed-abrasive polishing articles. Additional suitable processes that may be enhanced by the processes described herein include the commonly owned polishing processes disclosed in U.S. Patent No. 5,897,426, entitled, "Chemical Mechanical Polishing With Multiple Polishing articles," and U.S. Patent No. 6,435,945, entitled, "Chemical Mechanical Polishing With Multiple Polishing articles," ~~and U.S. Patent No. 6,435,935, and entitled, "Chemical Mechanical Polishing Processes and Components,"~~ the entirety of which are incorporated herein by reference to the extent not inconsistent with the invention.